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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: K. HORIKOSHI, et al.
Serial No.: 09/988,585
Filed: November 21, 2001
For: THIN-FILM TRANSISTOR AND METHOD OF
MANUFACTURING THE SAME
Art Group: 2811
Examiner: T. TRAN

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DSmalls/Logan
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TECHNOLOGY CENTER 2800

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AMENDMENT

Assistant Commissioner of Patents
Washington, D.C. 20231

December 19, 2002

Sir:

In response to the Office Action dated June 19, 2002, the period of response for which extension of time is requested in the attached Petition for Extension of Time, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SPECIFICATION:

On Page 3, please replace the third paragraph, beginning at line 7, with the following:

According to the above method disclosed in Japanese Patent Application Laid-open No. 8-195494, since the polycrystalline silicon layer is formed at a temperature of about 600°C, a usable glass substrate is limited to an annealed glass

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